

Product Summary

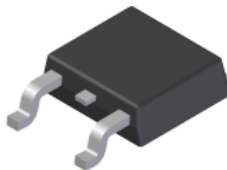
BV _{DSS}	R _{DS(ON)} MAX	I _D T _c = +25°C
-40V	11mΩ @ V _{GS} = -10V	-75A
	15mΩ @ V _{GS} = -4.5V	-65A

Description and Applications

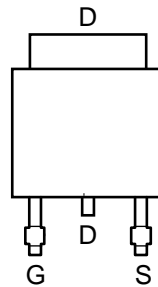
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC converters
- Power-management functions
- Analog switches

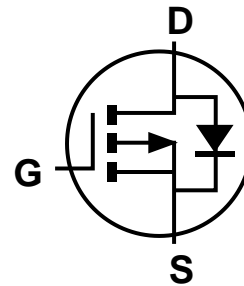
TO252 (DPAK)



Top View



Top View
Pin-Out



Equivalent Circuit

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMP4016SK3Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

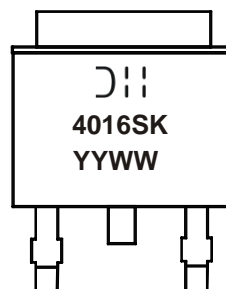
- Package: TO252
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓔ3
- Weight: 0.33 grams (Approximate)

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP4016SK3Q-13	TO252 (DPAK)	2,500	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



Ⓜ = Manufacturer's Marking
 4016SK = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 23 = 2023)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-40	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _C = +25°C T _C = +70°C	I _D	-75 -60	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	-300	A
Maximum Body Diode Continuous Current (Note 6)			I _S	-75	A
Pulsed Source Current (10μs Pulse, Duty Cycle = 1%)			I _{SM}	-300	A
Avalanche Current, L = 1mH			I _{AS}	-28	A
Avalanche Energy, L = 1mH			E _{AS}	392	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	31	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	P _D	113	W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	1.1	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-40	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -40V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-1.5	—	-2.5	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	6.8	11	mΩ	V _{GS} = -10V, I _D = -9.8A
		—	9.8	15		V _{GS} = -4.5V, I _D = -9.8A
Diode Forward Voltage	V _{SD}	—	-0.7	-1	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	5697	—	pF	V _{DS} = -20V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	534	—		
Reverse Transfer Capacitance	C _{rss}	—	408	—		
Gate Resistance	R _g	—	7	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	53	—	nC	V _{DS} = -20V, I _D = -9.8A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	112	—		
Gate-Source Charge	Q _{gs}	—	20	—		
Gate-Drain Charge	Q _{gd}	—	18	—		
Turn-On Delay Time	t _{D(ON)}	—	11.5	—	ns	V _{GS} = -10V, V _{DD} = -20V, R _G = 2Ω, I _D = -9.8A
Turn-On Rise Time	t _R	—	41	—		
Turn-Off Delay Time	t _{D(OFF)}	—	146	—		
Turn-Off Fall Time	t _F	—	165	—		
Reverse Recovery Time	t _{RR}	—	27	—	ns	I _F = -9.8A, di/dt = -100A/μs
Reverse Recovery Charge	Q _{RR}	—	22	—	nC	I _F = -9.8A, di/dt = -100A/μs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Device mounted on infinite heatsink.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

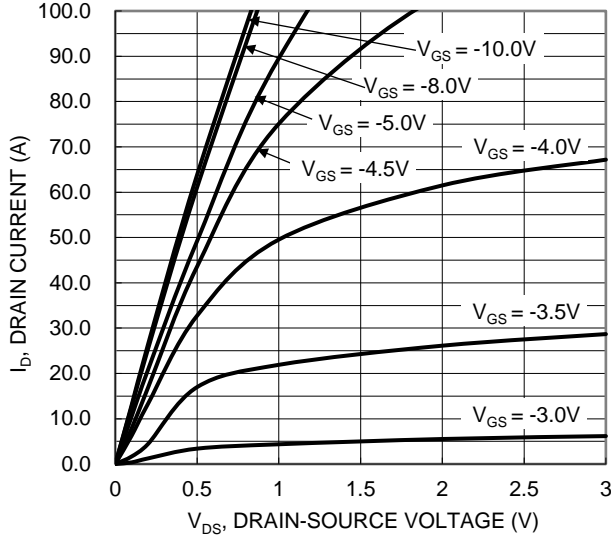


Figure 1. Typical Output Characteristic

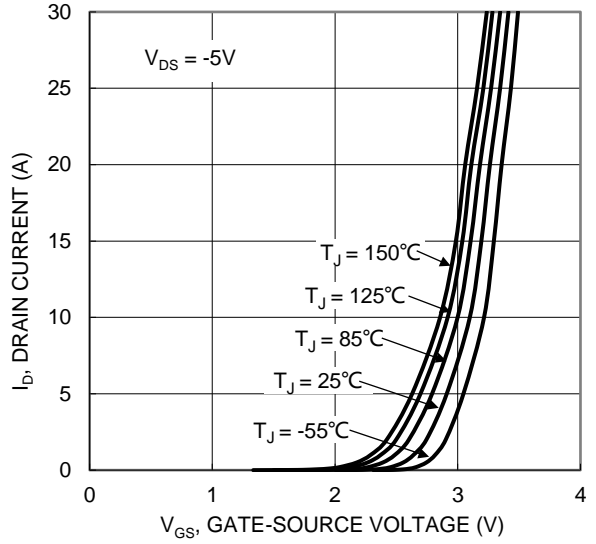


Figure 2. Typical Transfer Characteristic

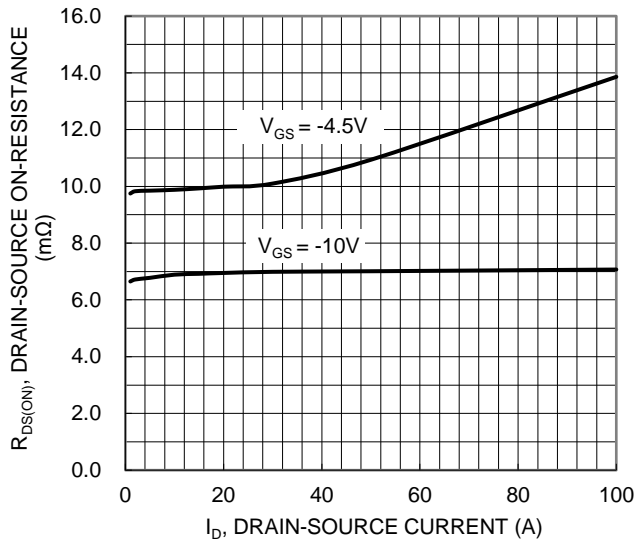


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

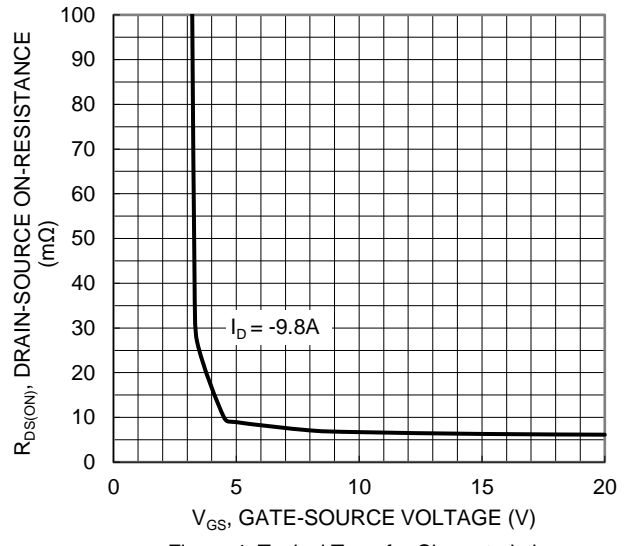


Figure 4. Typical Transfer Characteristic

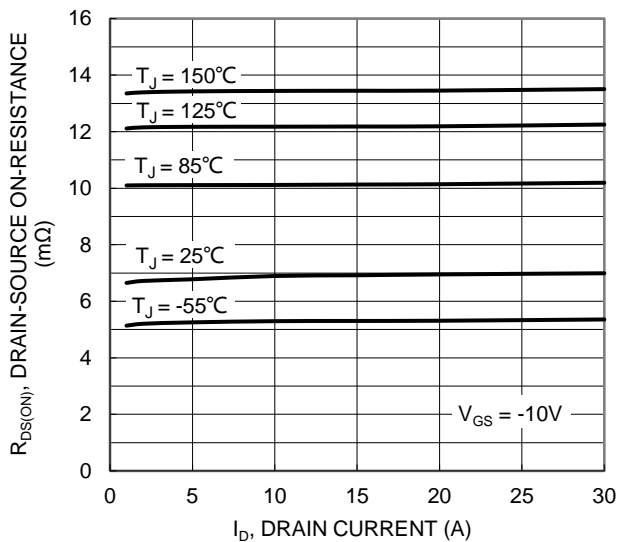


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

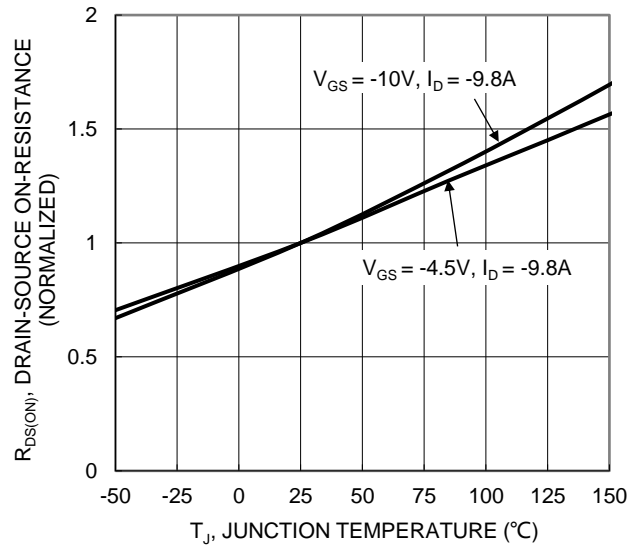


Figure 6. On-Resistance Variation with Temperature

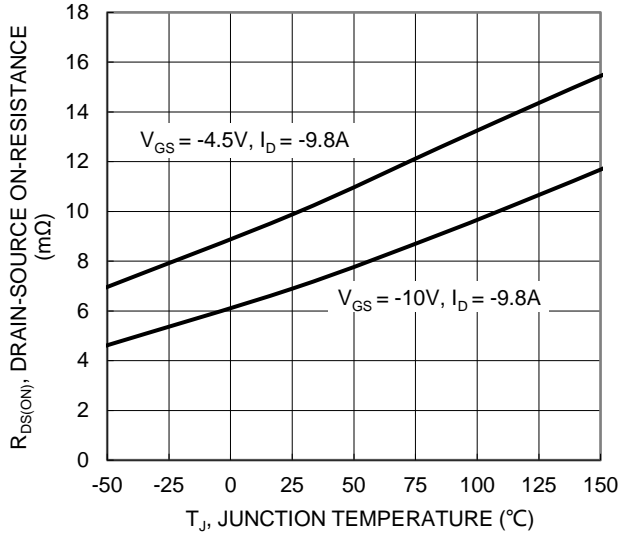


Figure 7. On-Resistance Variation with Temperature

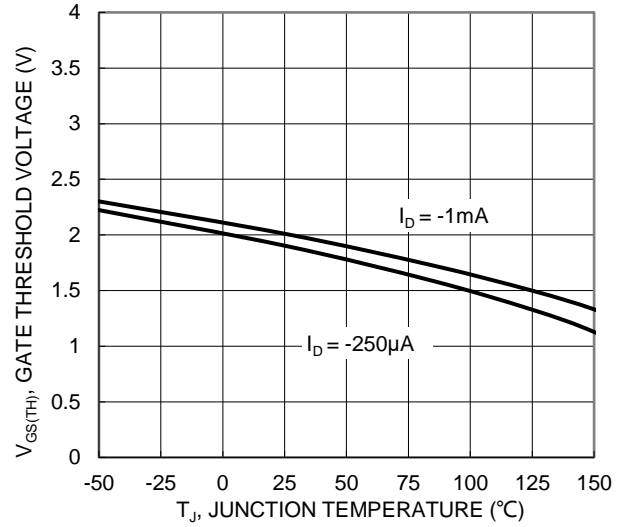


Figure 8. Gate Threshold Variation vs. Junction Temperature

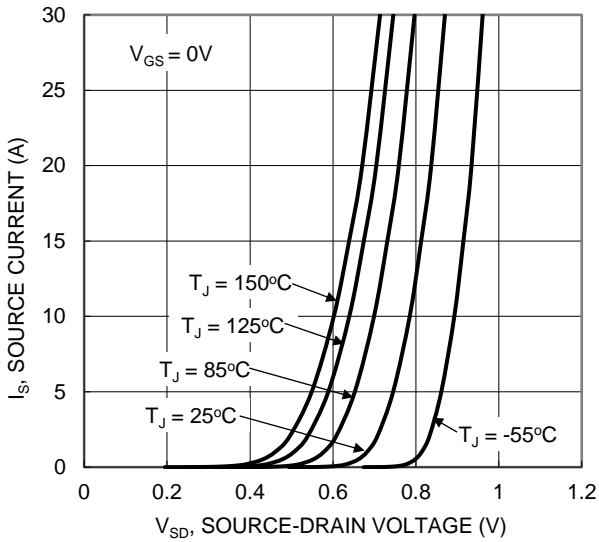


Figure 9. Diode Forward Voltage vs. Current

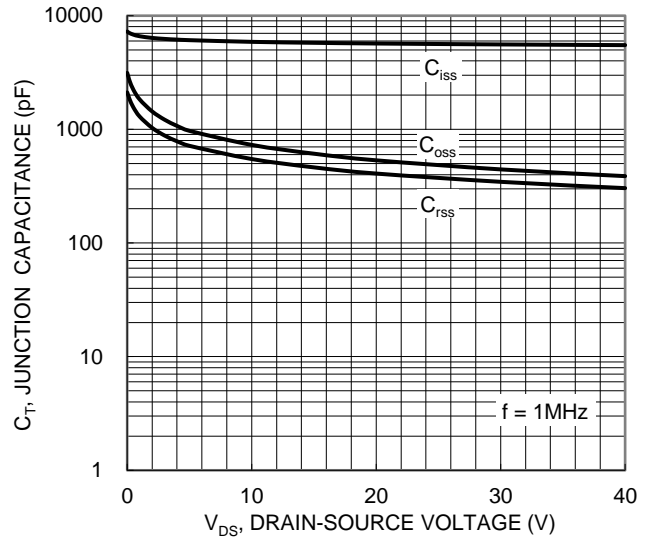


Figure 10. Typical Junction Capacitance

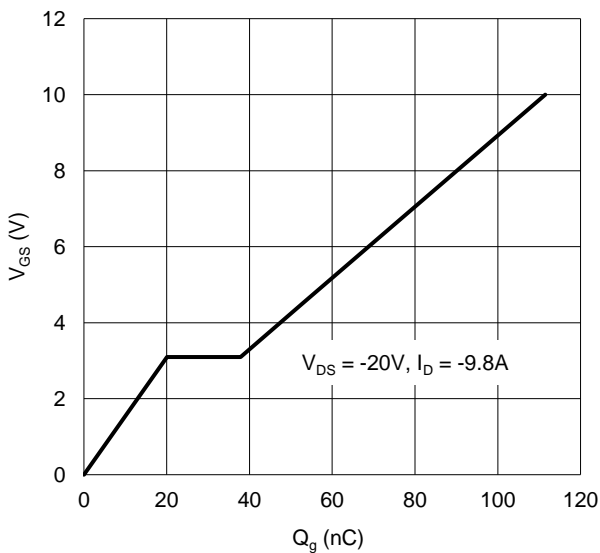


Figure 11. Gate Charge

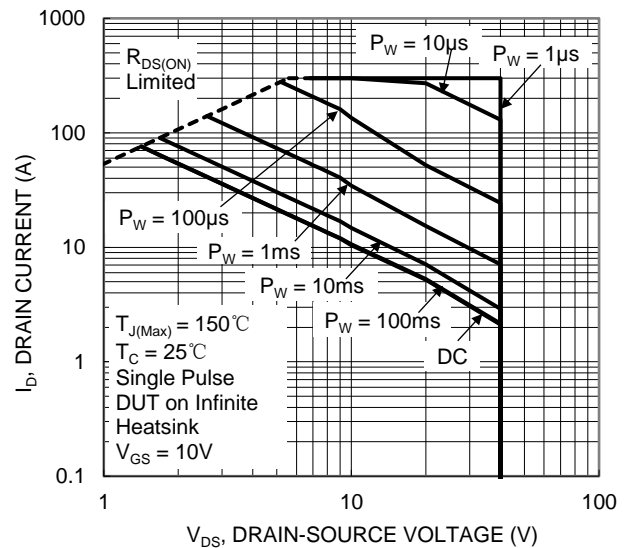


Figure 12. SOA, Safe Operation Area

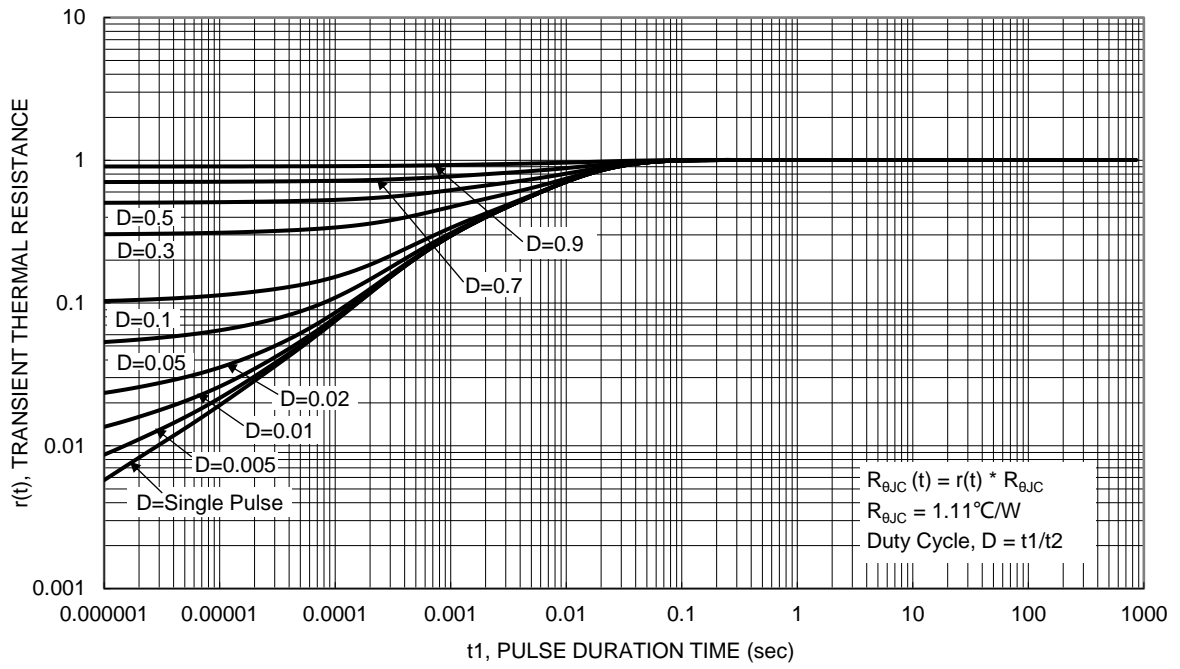
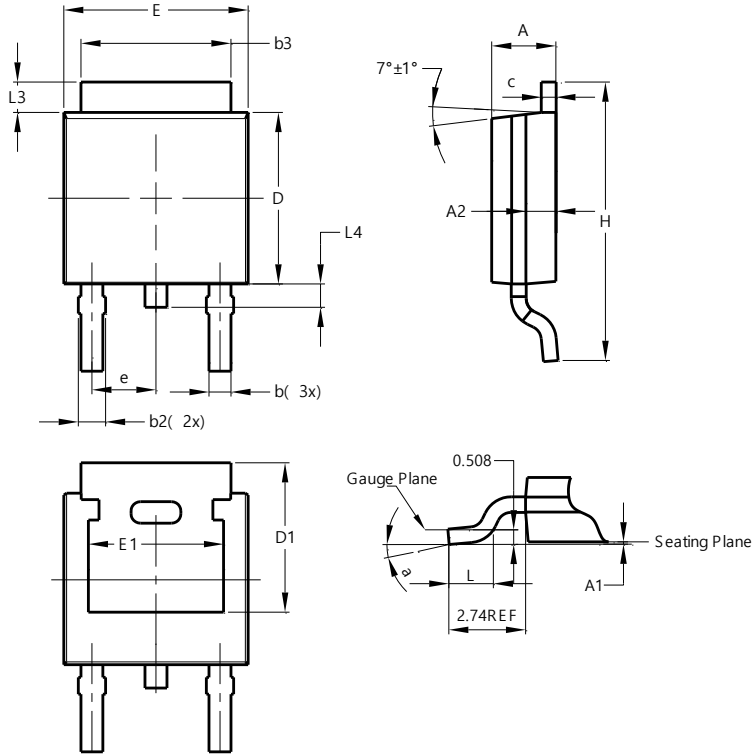


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

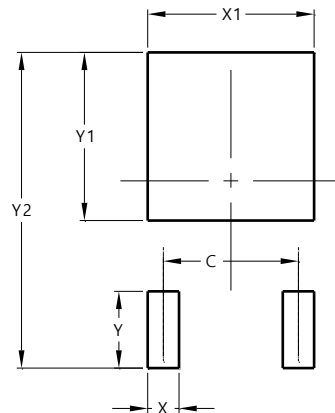


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.50	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	--	--
e	2.286 BSC		
E	6.45	6.70	6.58
E1	4.32	--	--
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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